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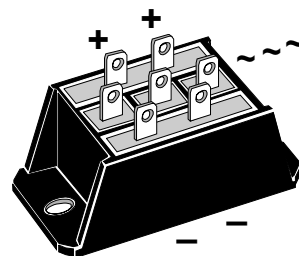
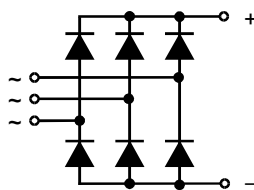
VUO 60

Three Phase Rectifier Bridge

$I_{dAV} = 72\text{ A}$
 $V_{RRM} = 1200-1800\text{ V}$

V_{RSM} V	V_{RRM} V	Type
1300	1200	VUO 60-12NO3
1500	1400	VUO 60-14NO3
1700	1600	VUO 60-16NO3
1900	1800	VUO 60-18NO3*

* delivery time on request



Symbol	Test Conditions	Maximum Ratings
I_{dAV} ①	$T_C = 85^\circ\text{C}$, module	72 A
I_{dAVM} ①	module	75 A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $V_R = 0$	t = 10 ms (50 Hz), sine 600 A t = 8.3 ms (60 Hz), sine 650 A
	$T_{VJ} = T_{VJM}$ $V_R = 0$	t = 10 ms (50 Hz), sine 540 A t = 8.3 ms (60 Hz), sine 600 A
I^2t	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0$	t = 10 ms (50 Hz), sine 1800 A ² s t = 8.3 ms (60 Hz), sine 1770 A ² s
	$T_{VJ} = T_{VJM}$ $V_R = 0$	t = 10 ms (50 Hz), sine 1460 A ² s t = 8.3 ms (60 Hz), sine 1510 A ² s
T_{VJ}		-40...+125 °C
T_{VJM}		125 °C
T_{stg}		-40...+125 °C
V_{ISOL}	50/60 Hz, RMS	t = 1 min 3000 V~ t = 1 s 3600 V~
	$I_{ISOL} \leq 1\text{ mA}$	
M_d	Mounting torque (M5) (10-32 UNF)	2-2.5 Nm 18-22 lb.in.
Weight	typ.	50 g

Features

- Package with DCB ceramic base plate
- Isolation voltage 3600 V~
- Planar passivated chips
- Blocking voltage up to 1800 V
- Low forward voltage drop
- 1/4" fast-on terminals
- UL registered E 72873

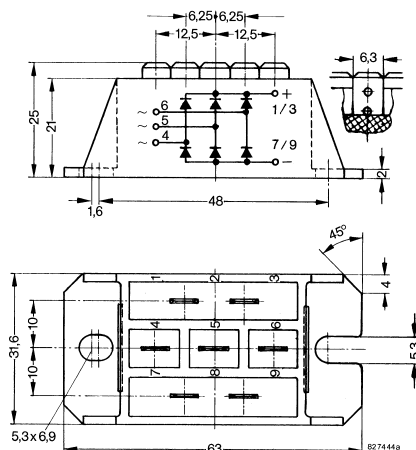
Applications

- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Rectifier for DC motors field current

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling

Dimensions in mm (1 mm = 0.0394")



Symbol	Test Conditions	Characteristic Values
I_R	$V_R = V_{RRM}$; $T_{VJ} = 25^\circ\text{C}$	0.3 mA
	$V_R = V_{RRM}$; $T_{VJ} = T_{VJM}$	5 mA
V_F	$I_F = 150\text{ A}$; $T_{VJ} = 25^\circ\text{C}$	1.9 V
V_{T0}	For power-loss calculations only	0.8 V
r_T		6.5 mΩ
R_{thJC}	per diode, DC current	1.2 K/W
	per module	0.2 K/W
R_{thJH}	per diode, DC current	1.6 K/W
	per module	0.27 K/W
d_s	Creep distance on surface	10 mm
d_A	Strike distance in air	9.4 mm
a	Max. allowable acceleration	50 m/s ²

Data according to IEC 60747 and refer to a single diode unless otherwise stated.

① for resistive load at bridge output

IXYS reserves the right to change limits, test conditions and dimensions.

Use output terminals in parallel connection!

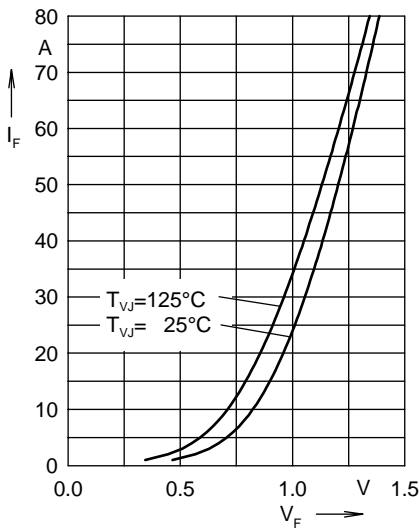


Fig. 4 Forward current versus voltage drop per diode

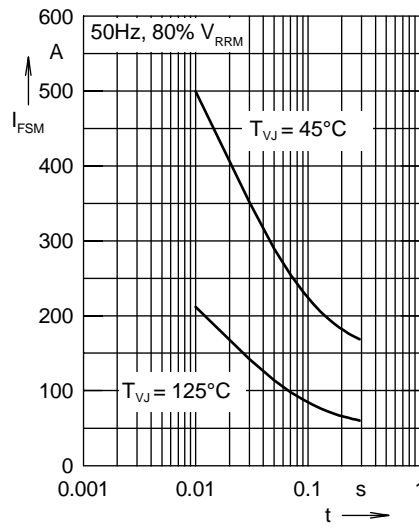


Fig. 5 Surge overload current

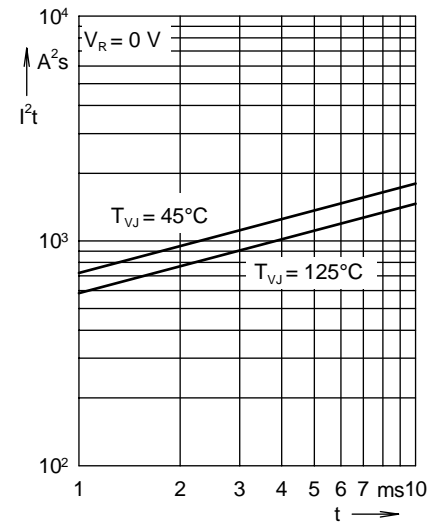


Fig. 6 I^2t versus time per diode

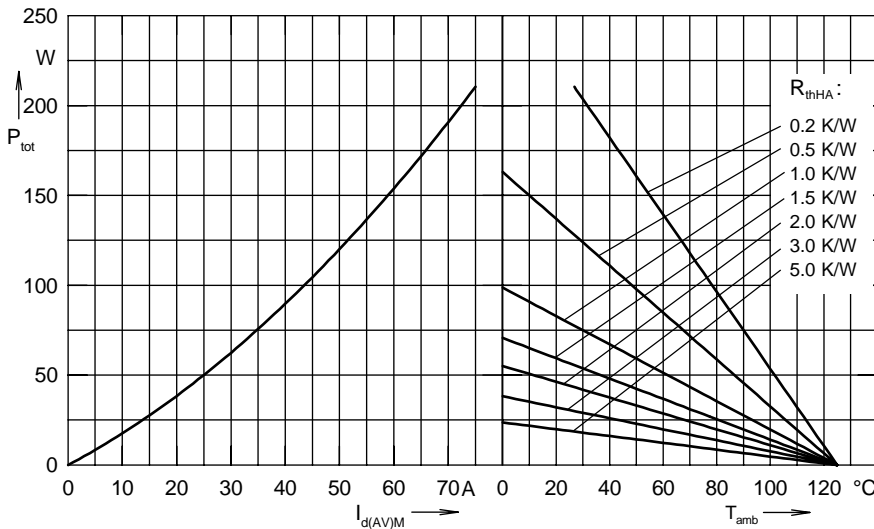


Fig. 7 Power dissipation versus direct output current and ambient temperature

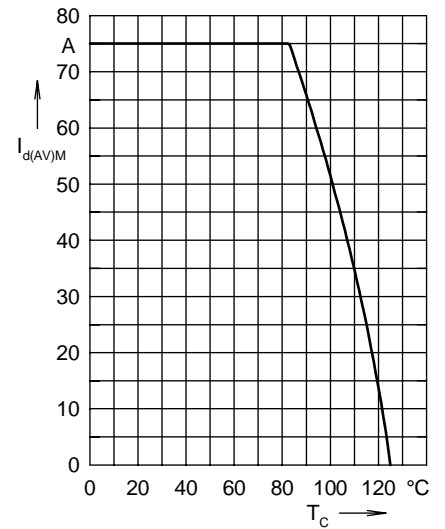


Fig. 8 Max. forward current versus case temperature

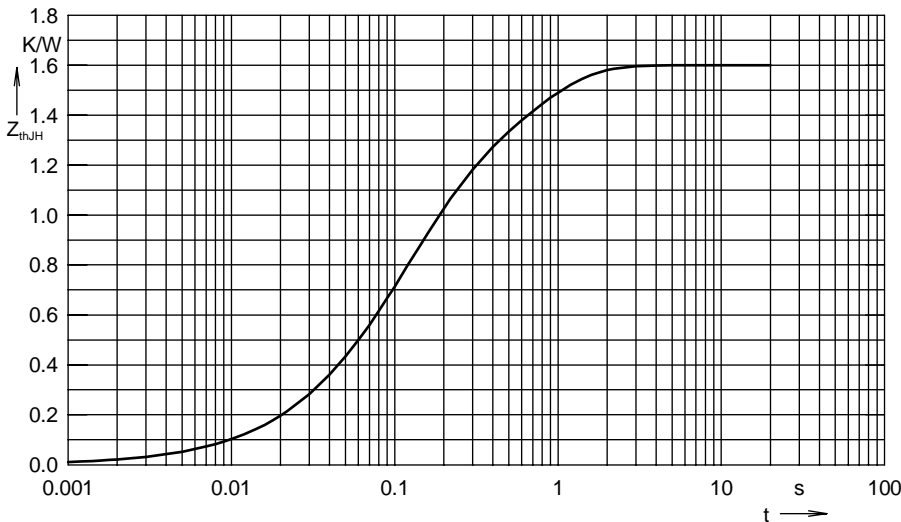


Fig. 9 Transient thermal impedance junction to heatsink

Constants for Z_{thJH} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.883	0.102
2	0.098	0.103
3	0.202	0.492
4	0.417	0.62